

Radiation Induced Segregation (RIS) + Defects

K.G. Field^{1,a},

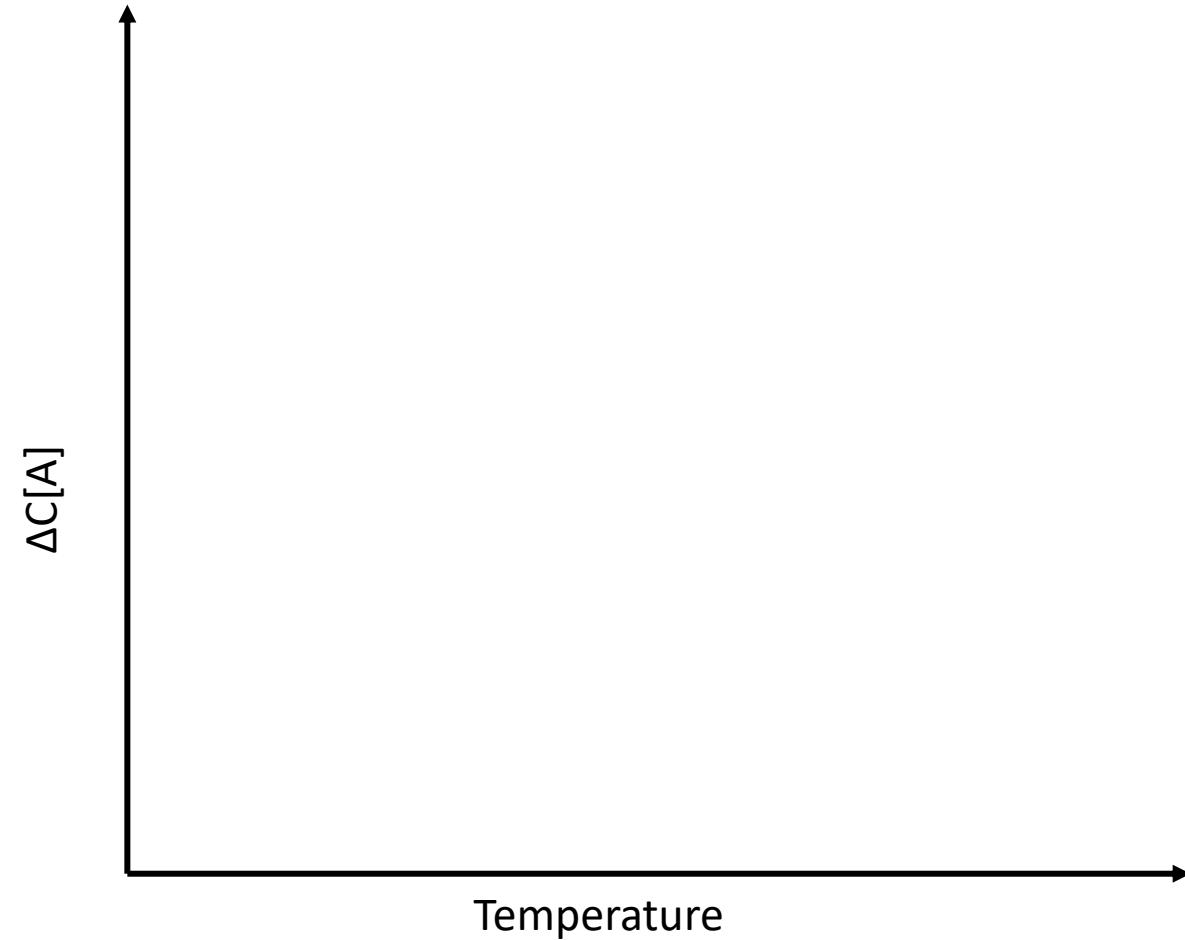
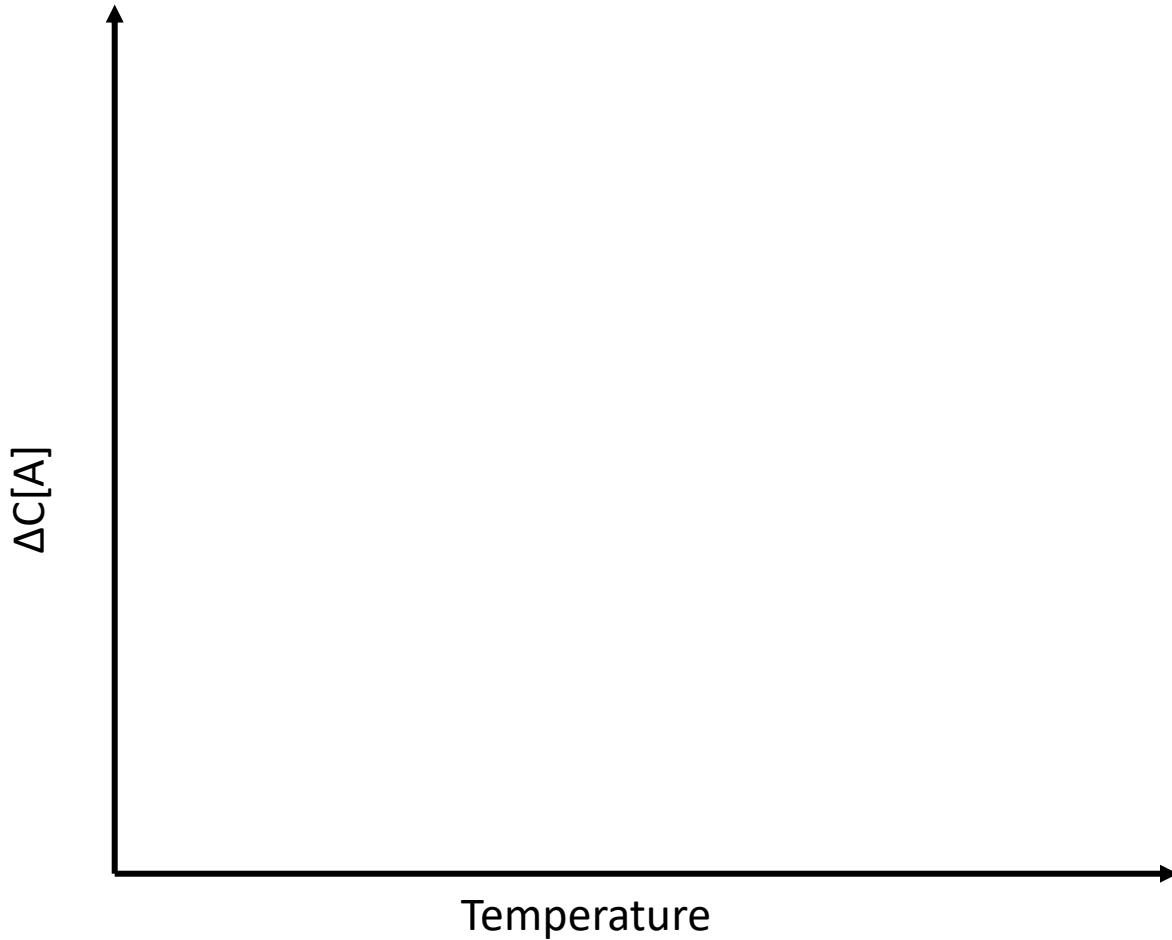
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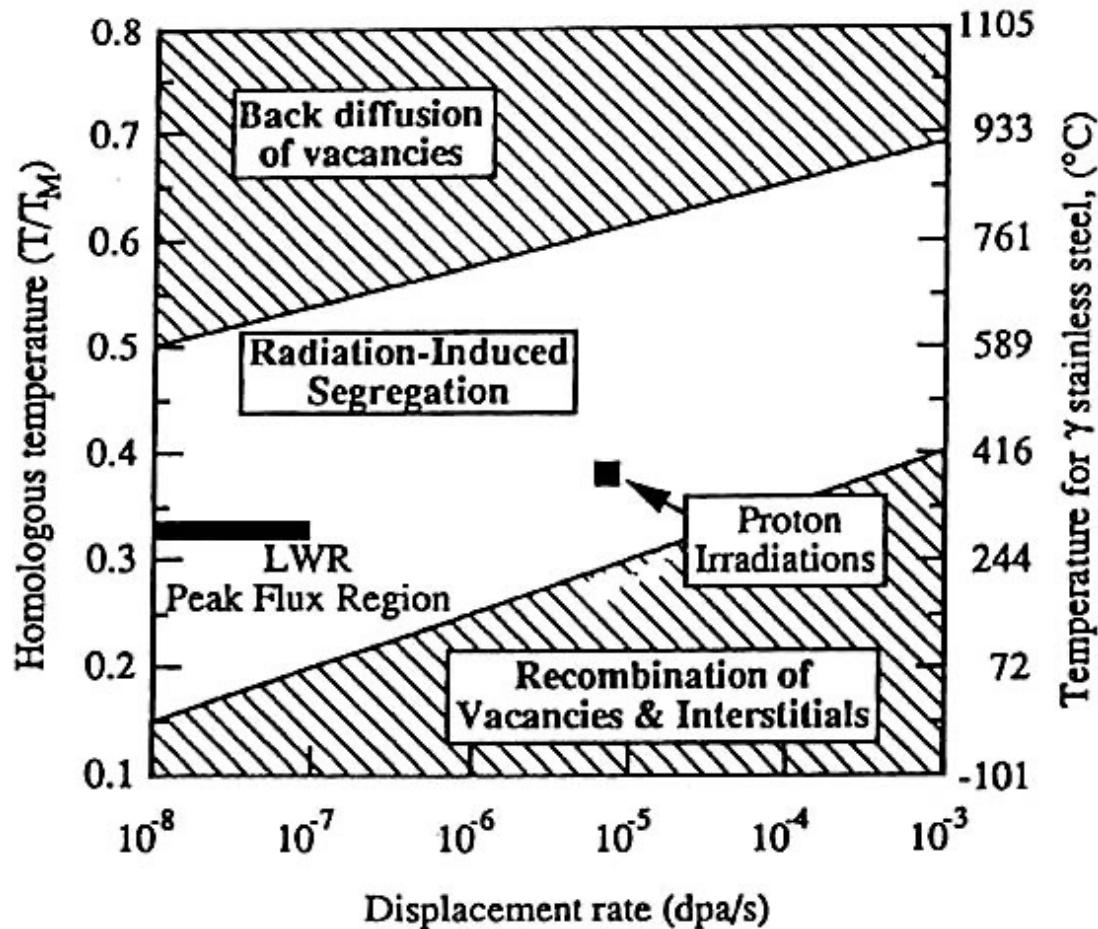


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Last lecture we talked about RIS



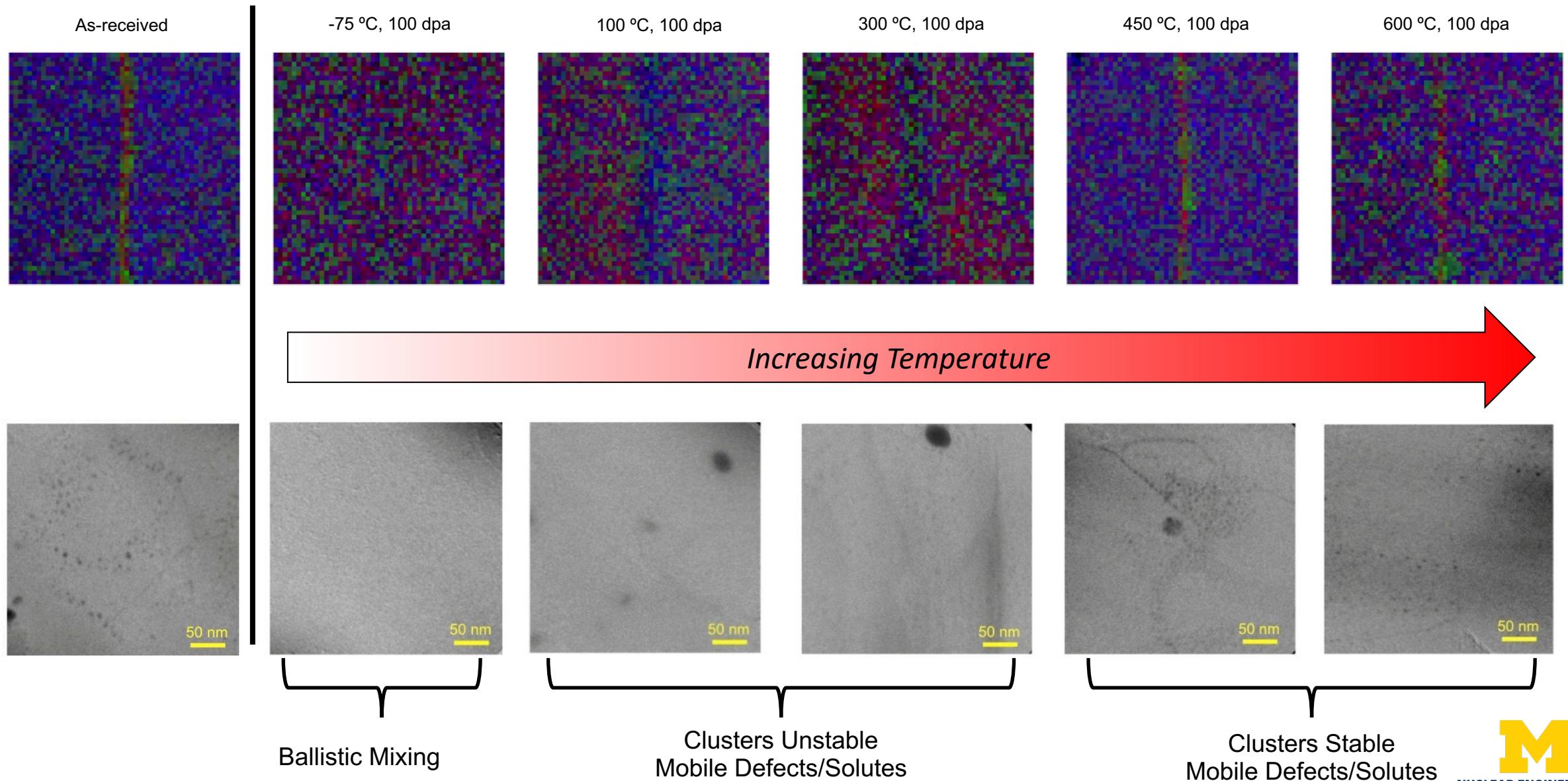
Last lecture we talked about RIS



$$\nabla C_A = \frac{N_A N_B d_{Bi} d_{Ai}}{\alpha(d_{Bi} N_B D_A + d_{Ai} N_A D_B)} \times \left(\frac{d_{Av}}{d_{Bv}} - \frac{d_{Ai}}{d_{Bi}} \right) \nabla C_v$$



RIS is a “finger print” for defect mobility and loss



Outline

Defect Energetics:

- Role of loops on material response
- Interstitial loop formation and energetics
- Vacancy loop vs. void formation

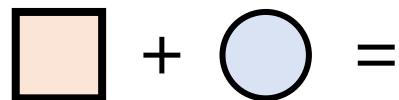
Goal:

1. Understand the energetics associated with the formation of extended defects and the corresponding responses as a function of temperature and dose/dose rate.

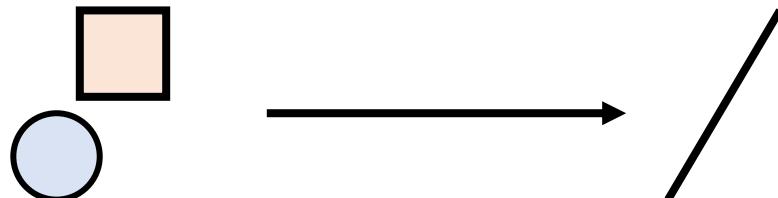


Options of vacancies and interstitials

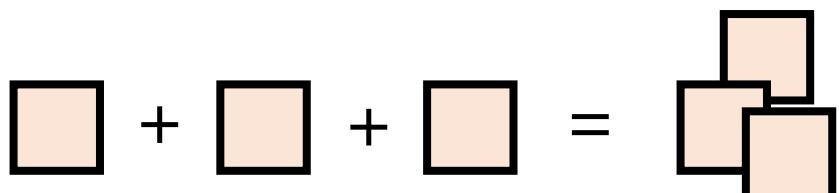
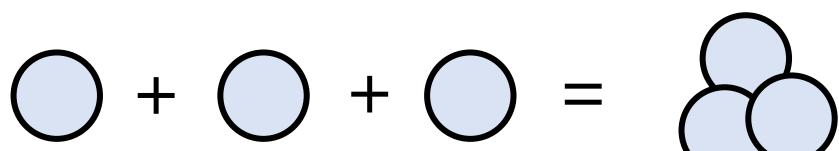
- Vacancies and interstitials can react with each other (recombination)



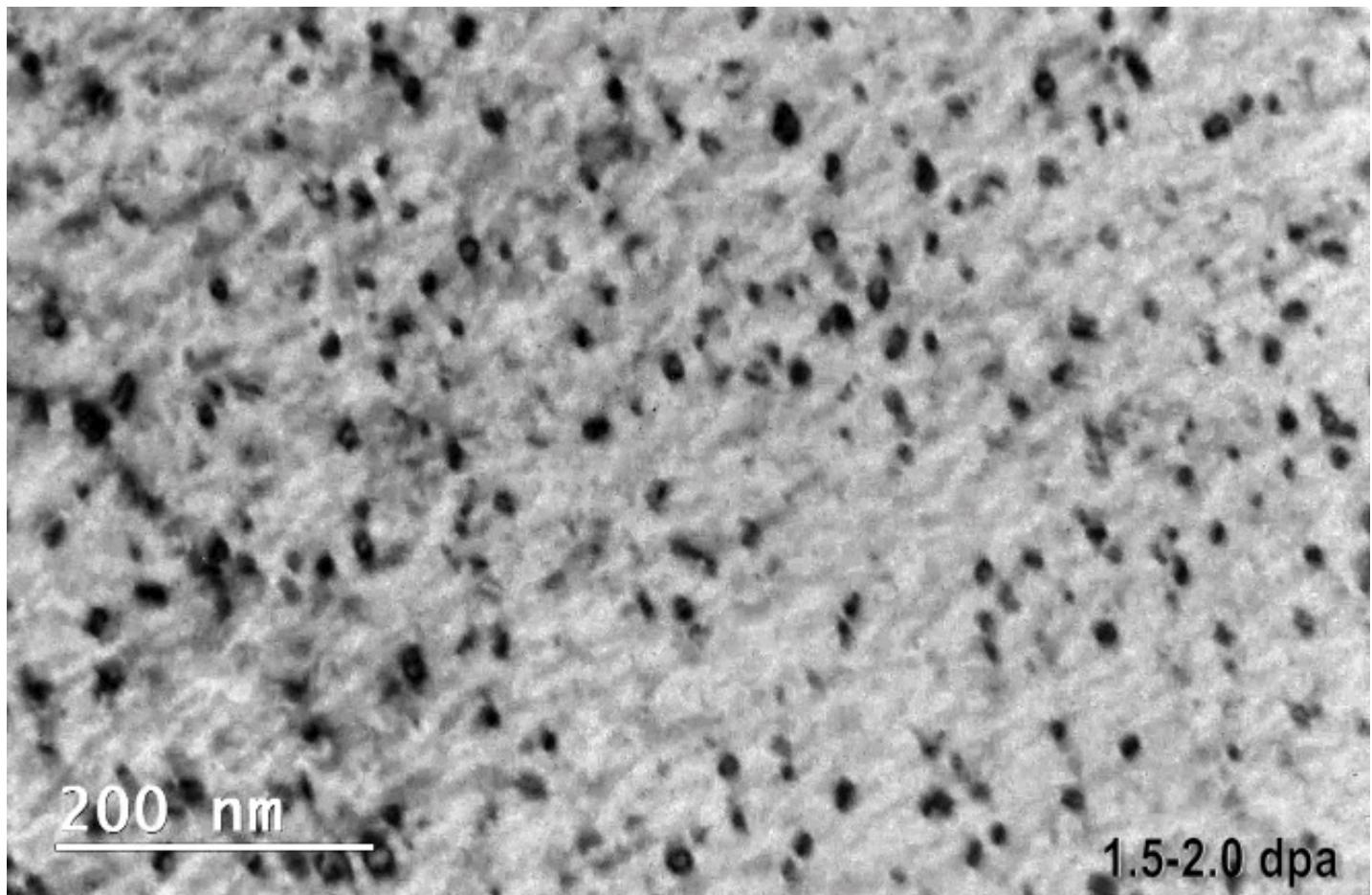
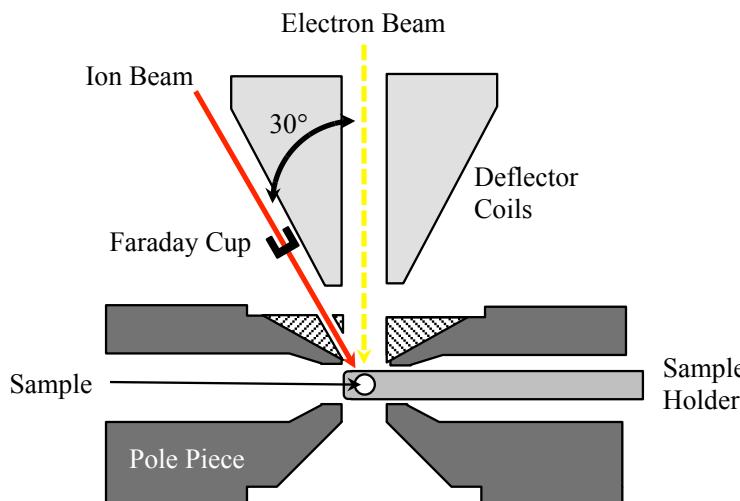
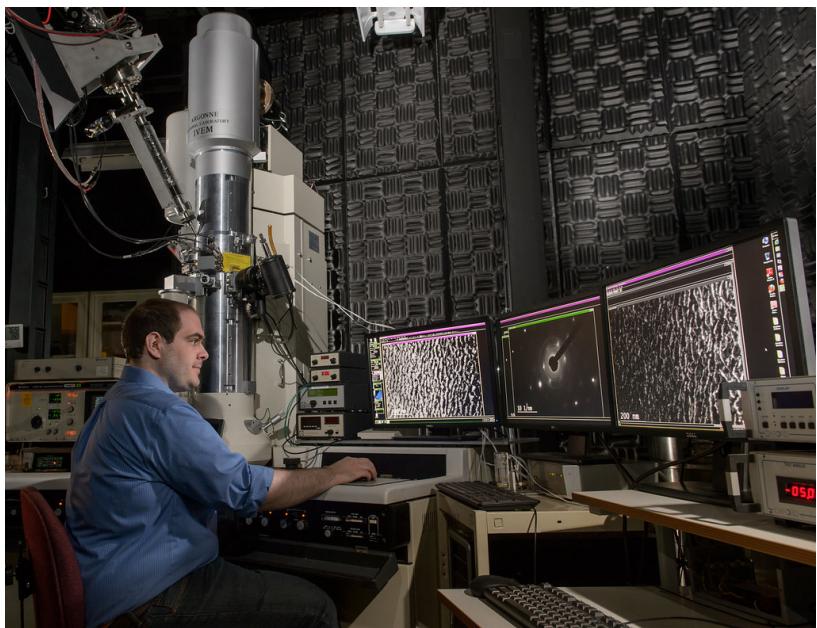
- They can react with defect sinks



- They can react with themselves



Dislocation Loop Formation

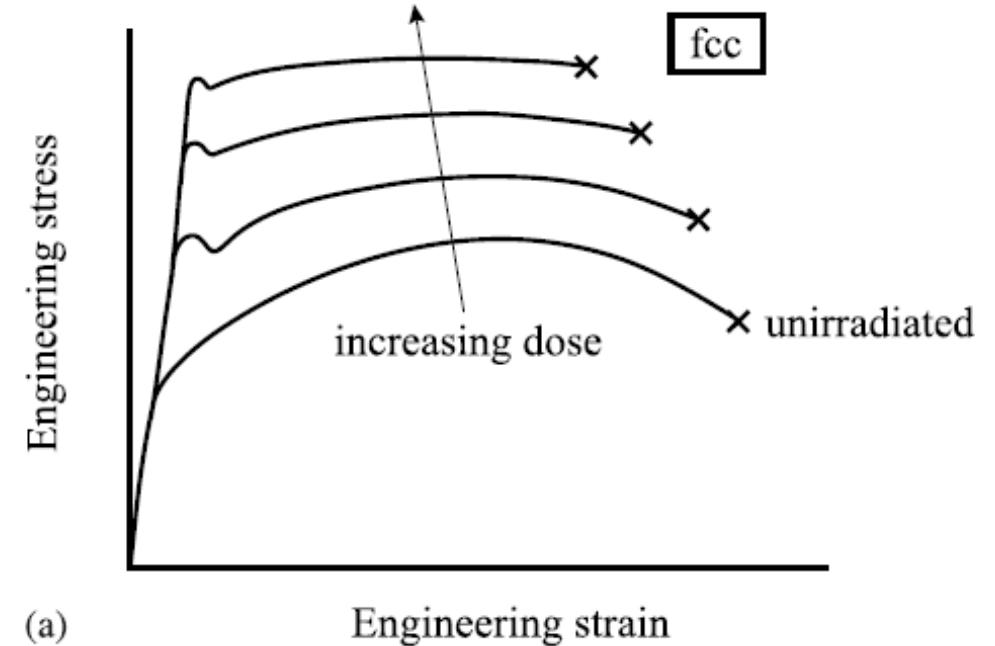
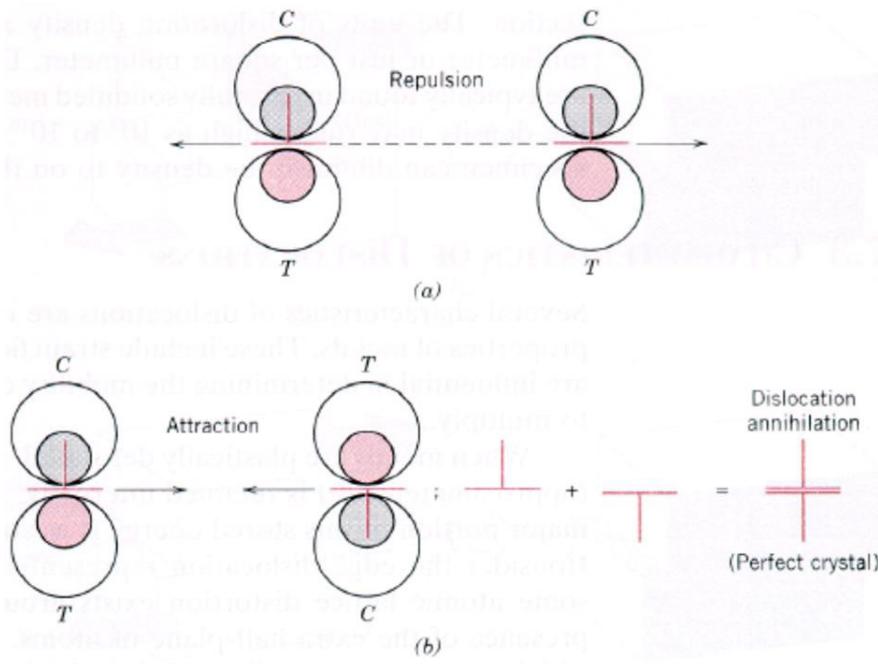


Video of in-situ ion irradiation of Fe-10Cr-4.8Al Gen I alloy irradiated at 320°C



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Effects of dislocation loops on mechanical properties



- Slowing down or impeding dislocation motion in metals results in **hardening** but can also lead to **embrittlement**
- Dislocation loop formation by irradiation will cause this hardening and embrittlement response



Dislocation Loop Formation

- In any crystal lattice there are close packed planes (e.g. most densely packed)
 - Normal to the closed pack plane is lattice planes that are widely separated
- Loops can be considered as a condensation of radiation-produced vacancies or interstitials

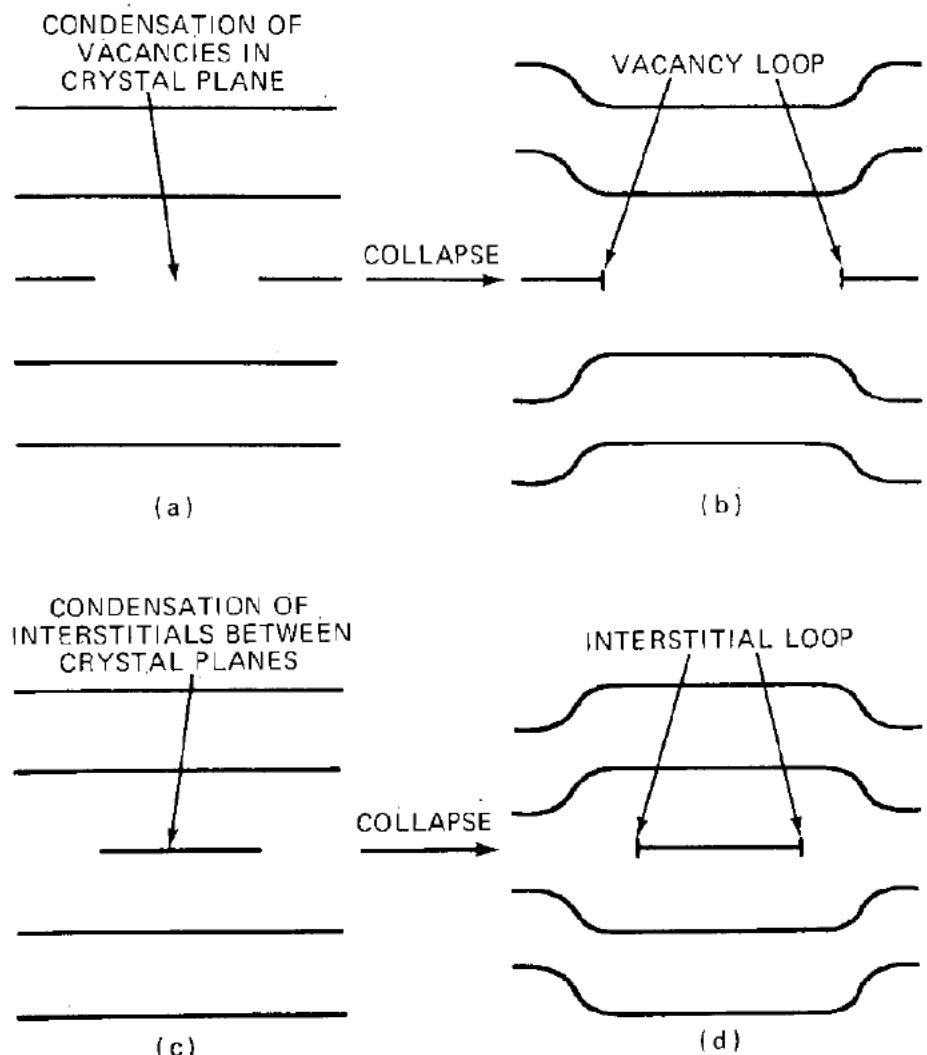
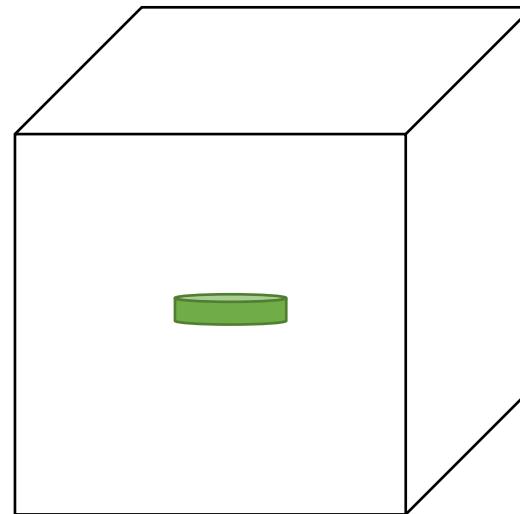
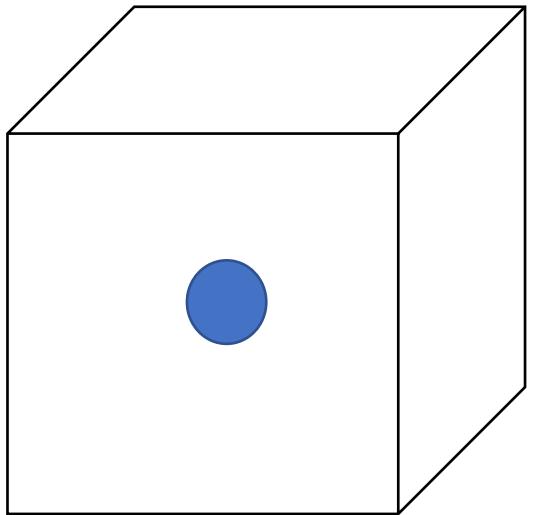


Fig. 18.4 Formation of vacancy loops and interstitial loops.

A simple though experiment



If we placed a sphere and a disc into a finite volume of material, what aspects of those features would help define the change in energy for the total system?

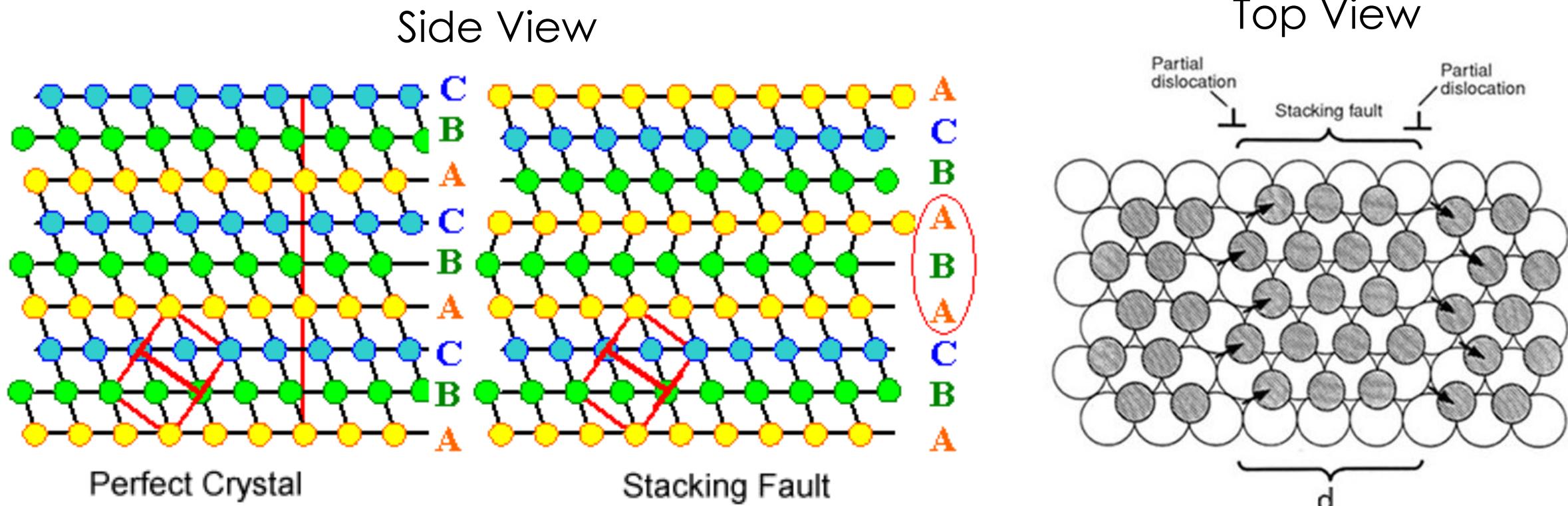


Dislocation Loop Formation

- Loops formed from interstitial atoms or vacancies can be distinguished in three ways:
 1. The **Burgers vector** (magnitude and direction)
 2. The **stacking fault** (if any) contained by the loop
 3. The **nature** (e.g. vacancy or interstitial loops)

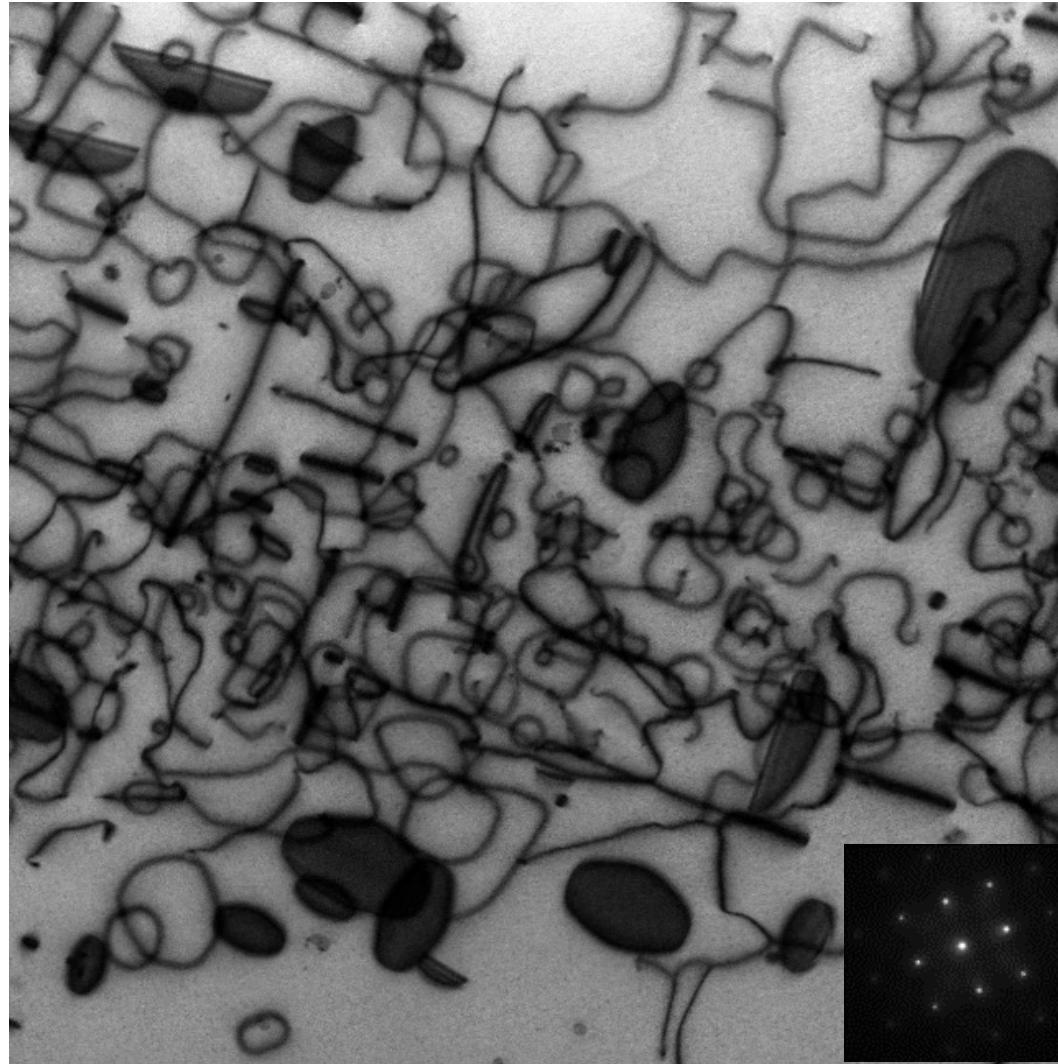
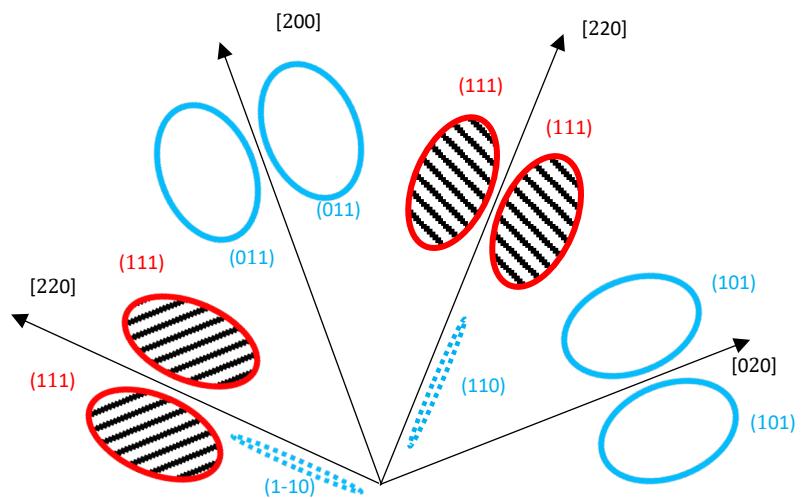


What is a stacking fault?



- The shifted portion of the partial dislocation location is a “stacking fault”
 - more simply it is a “mistake” in the layering of atoms
- Found in closed-packed face centered cubic and hcp crystals because only the second-nearest neighbors are different at the fault

Dislocation loop energy in FCC alloys



What year was the last time
that a British constructor didn't
have a 1st place win in the F1
championship season?



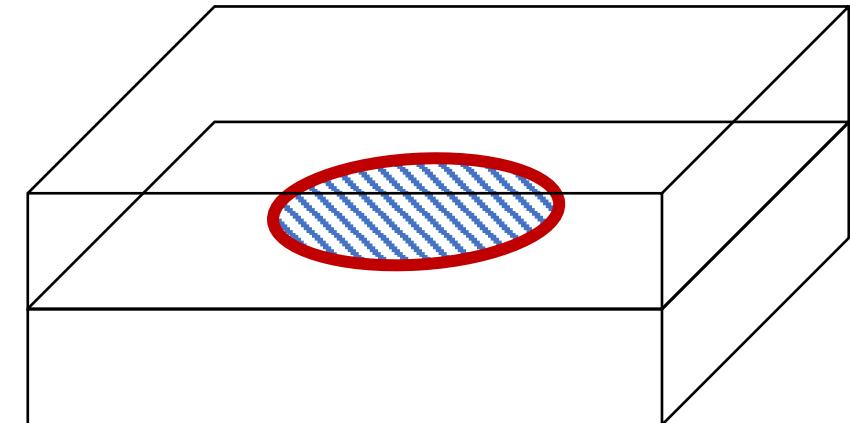
Interstitial Loops Formation

- Let's first consider interstitial loop formation:
- Formation of extended defects occurs between closed packed planes
- In FCC materials, this can cause a break in the stacking sequence leading to stacking faults (also known as Frank loops)
- Disc/platelet of defects it the minimum energy configuration for defect clusters when the number of defects is small



Dislocation loop energy in FCC alloys

- For FCC, we must consider both the energy created because of the loop and of the possible stacking fault:



Dislocation loop energy in FCC alloys

- For an FCC crystal we can typically see two loop types:

- Faulted:

$$E_L^f = 2\pi r_L \Gamma + \pi r_L^2 \gamma_{SFE}$$



Writing in terms of materials constants we get:

$$E_L^f = \frac{2}{3} \frac{1}{(1-v)} \mu b^2 r_L \left[\ln \frac{4r_L}{r_0} - 2 \right] + \pi r_L^2 \gamma_{SFE}$$

- Perfect:

$$E_L^p = \left[\frac{2}{3} \frac{1}{(1-v)} + \frac{1}{3} \left(\frac{2-v}{2(1-v)} \right) \right] \mu b^2 r_L \left[\ln \frac{4r_L}{r_0} - 2 \right]$$

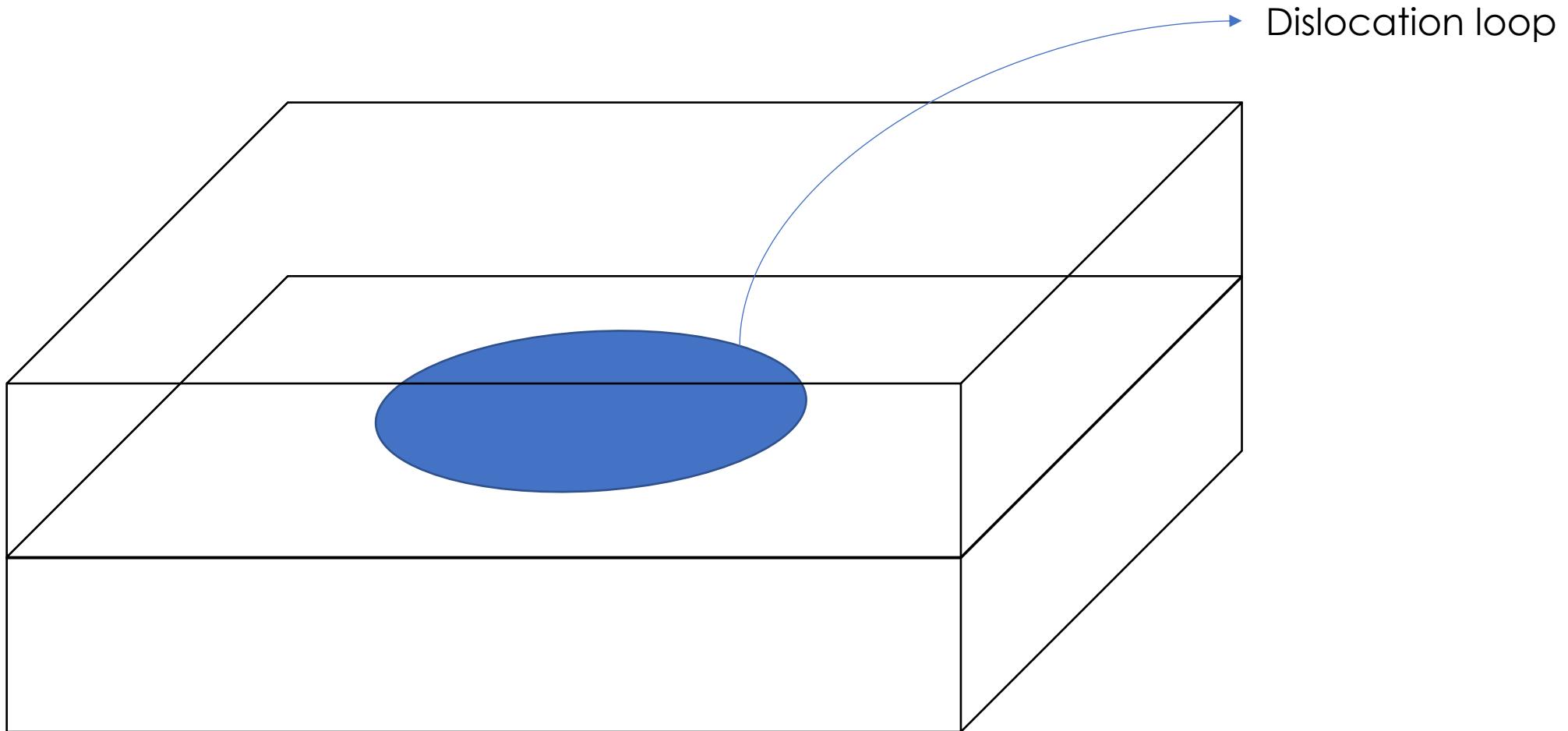


Dislocation loop energy in FCC alloys

$$\gamma_{SFE} > \frac{\mu b^2}{3\pi r_L} \left(\frac{2 - \nu}{2(1 - \nu)} \right) \ln \left[\frac{4r_L}{r_0} - 2 \right]$$

Metal/Alloy	γ (mJm^{-2})	Reference
SS-304	21	Murr 1975, Hadji & Badji 2002
SS-316	42	Hadji & Badji 2002
Ni	128	Murr 1975
Ti	15	Conrad 1981
Al	166	Murr 1975
Zr	240	Murr 1975

A simple loop growth model



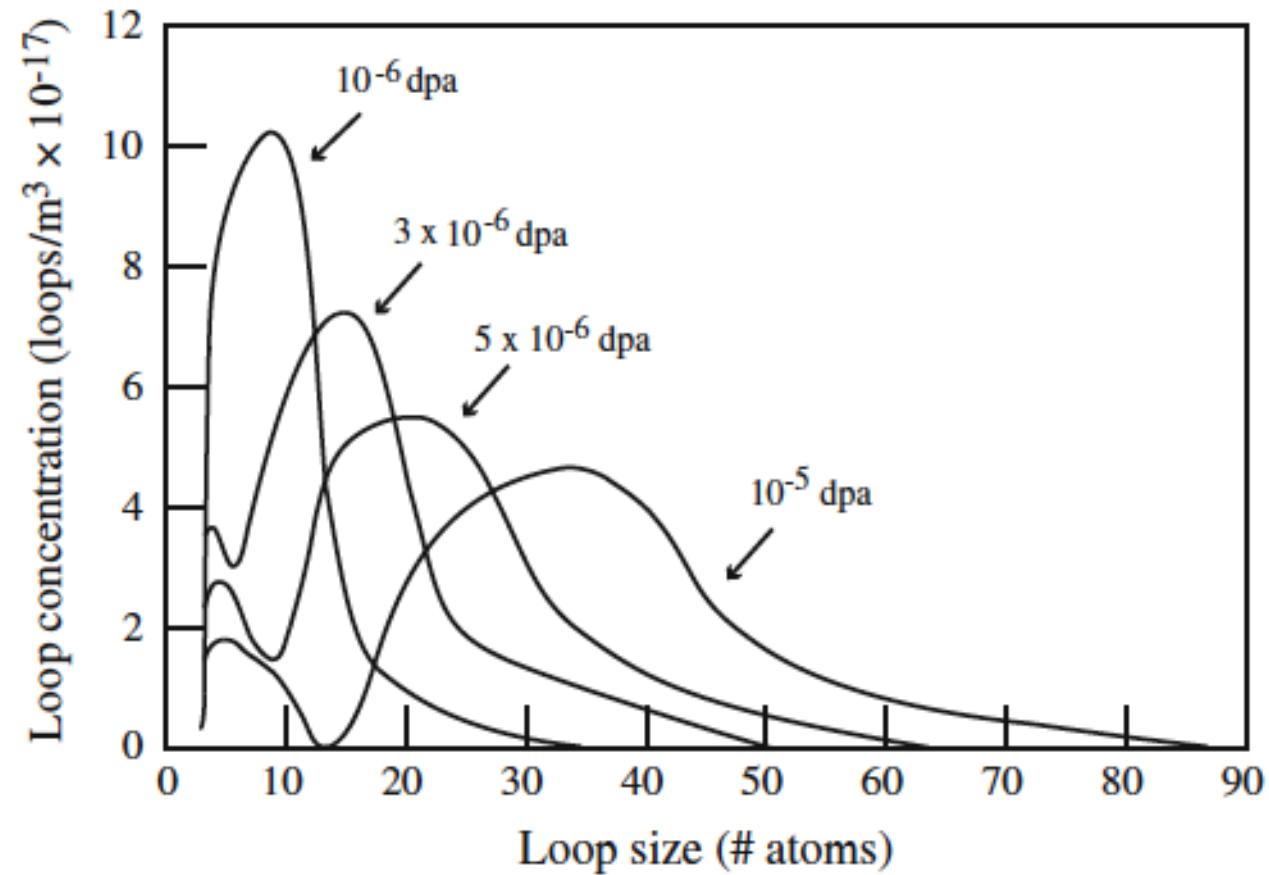
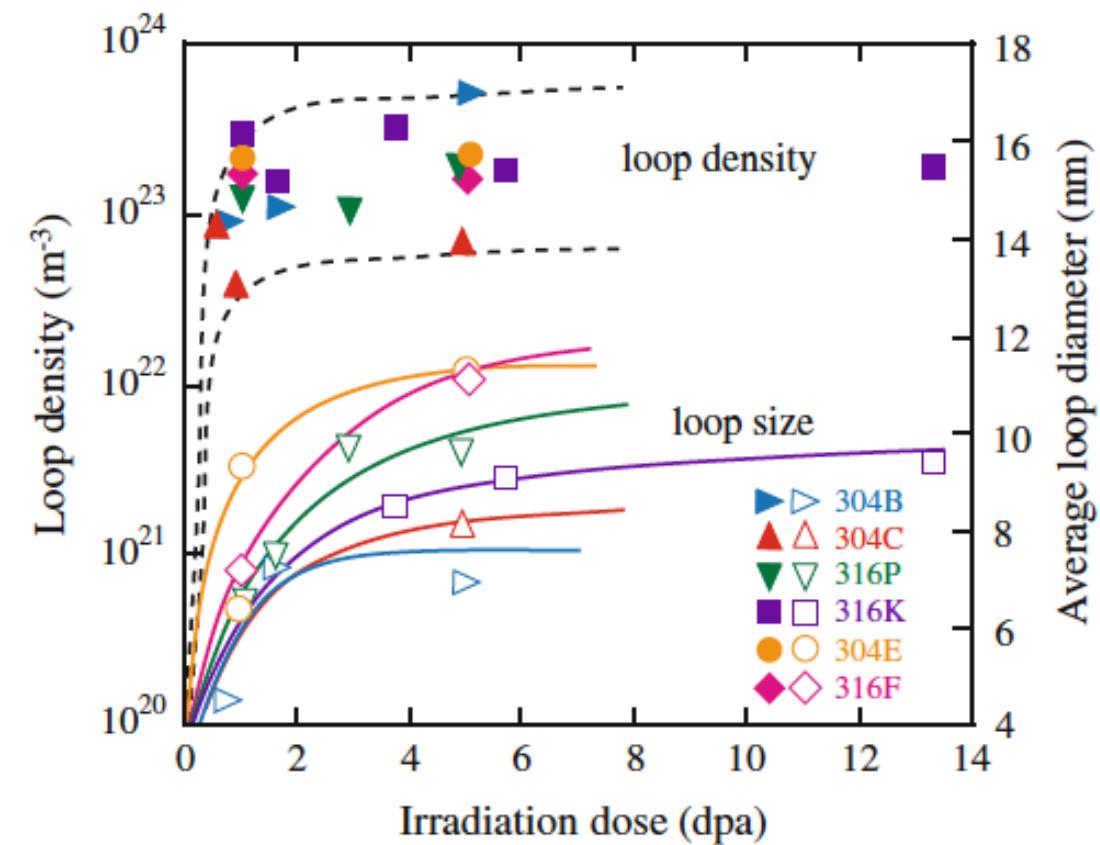
A simple loop growth model

$$\left(\frac{dr_L}{dt}\right)_v = \frac{1}{b} \left[D_v C_v - Z_i D_i C_i - D_s^v \exp\left(\frac{\tau b^2}{r_L k_b T}\right) + D_s^i \exp\left(-\frac{\tau b^2}{r_L k_b T}\right) \right]$$

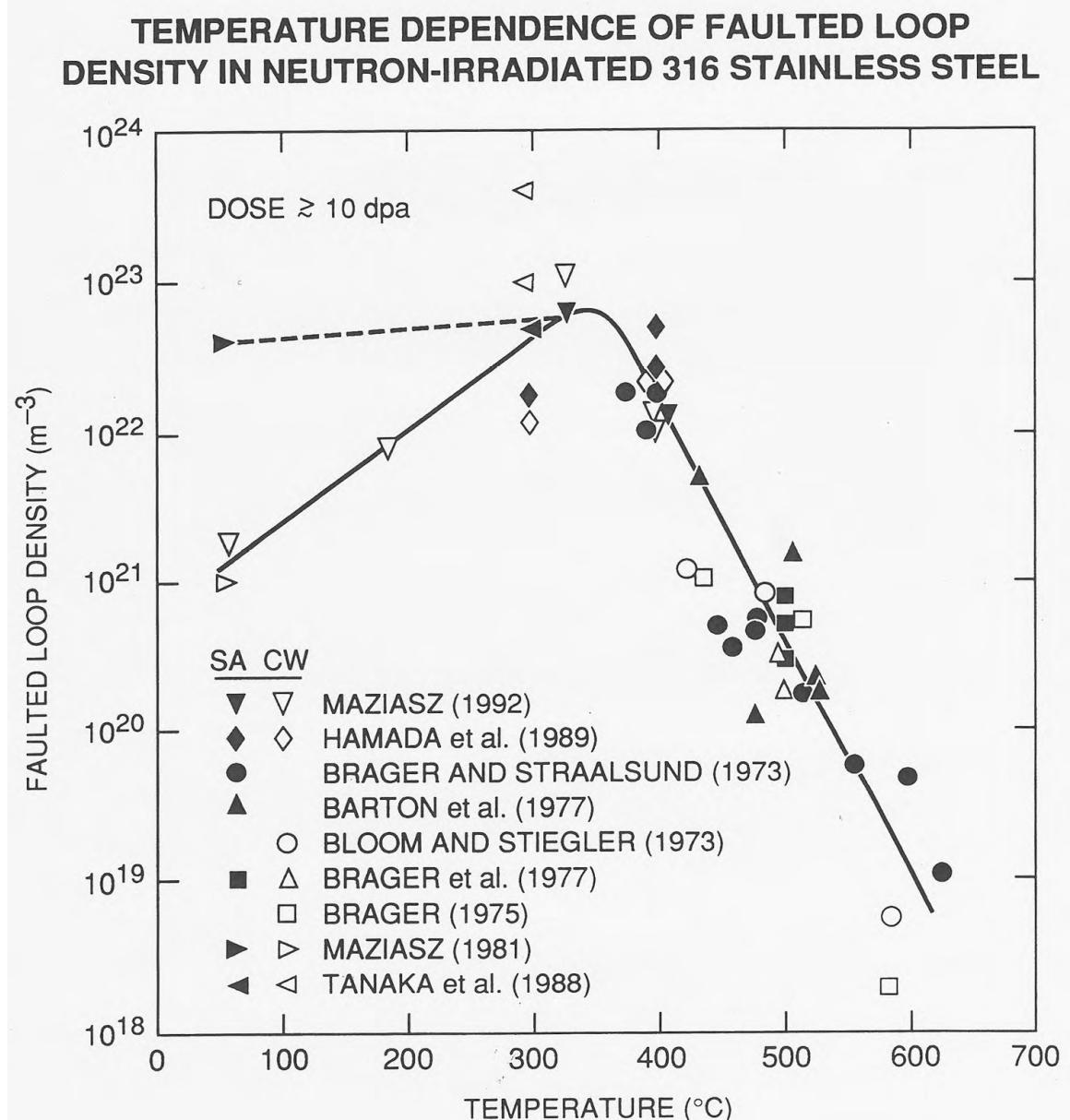
$$\left(\frac{dr_L}{dt}\right)_i = \frac{1}{b} \left[Z_i D_i C_i - D_v C_v - D_s^i \exp\left(\frac{\tau b^2}{r_L k_b T}\right) + D_s^v \exp\left(-\frac{\tau b^2}{r_L k_b T}\right) \right]$$



Dose dependence



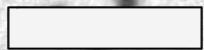
Temperature dependence



Zinkle, Maziasz & Stoller, JNM 206 (1993) 266



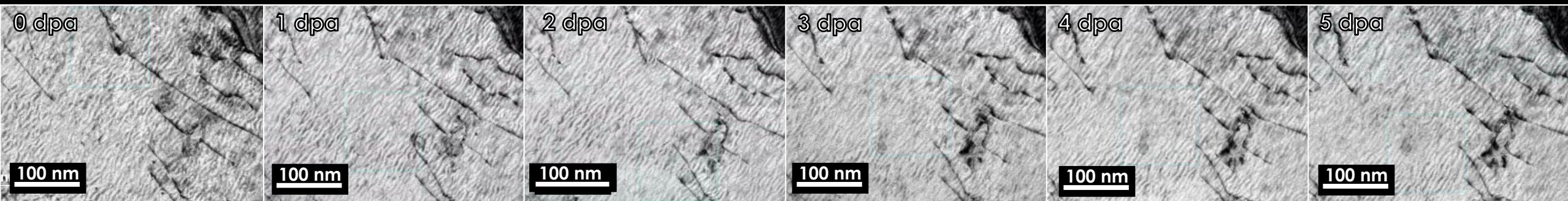
Image Stitching



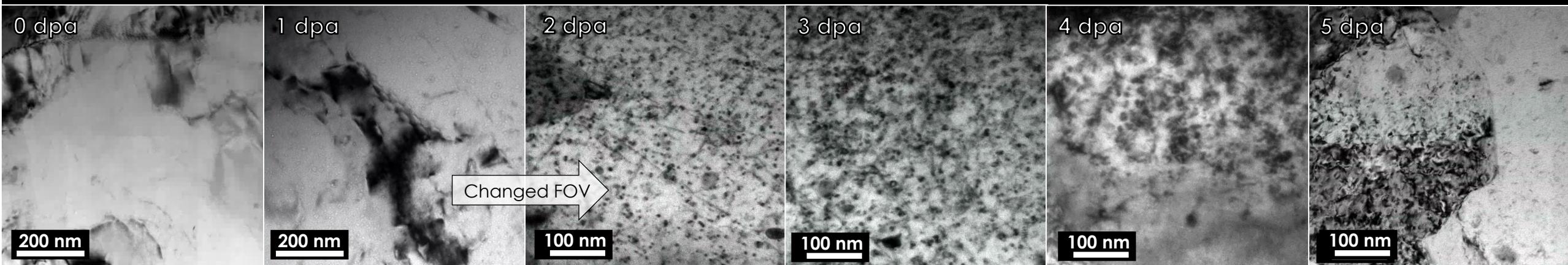
100 nm

In situ imaging conditions: [100] zone axis, $g = <110>$

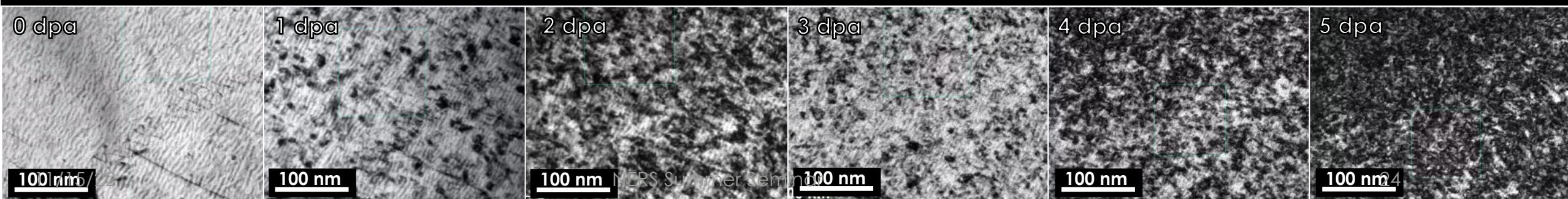
5 dpa



5 dpa + 1,000 appm He/dpa

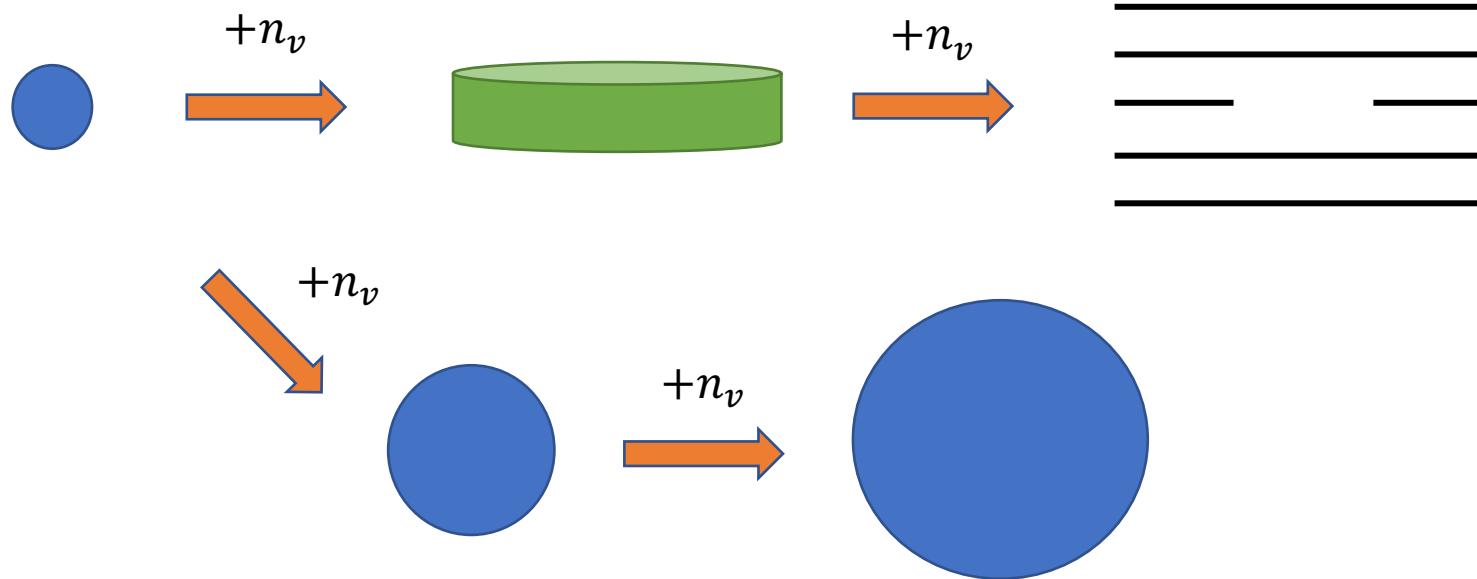


5 dpa + 3,333 appm He/dpa



MERS Summer School

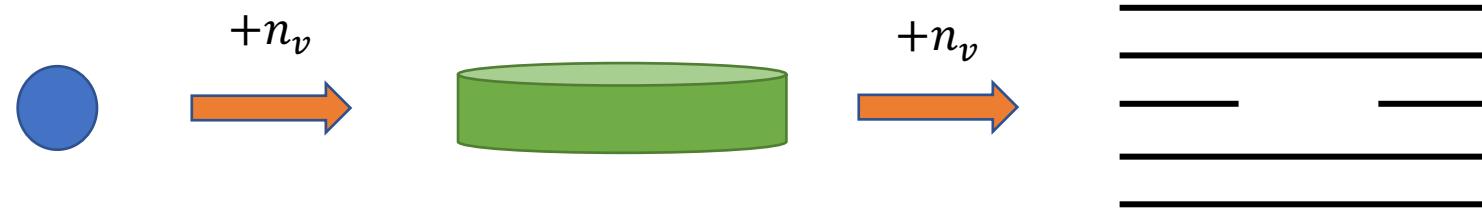
Now let's consider vacancy condensation



$$E_s = 4\pi r^2 \sigma \rightarrow E_c = 2\pi r^2 \sigma$$

- For the same n_v , $E_c > E_s$ meaning an activation energy is required to generate large spherical voids

Now let's consider vacancy condensation

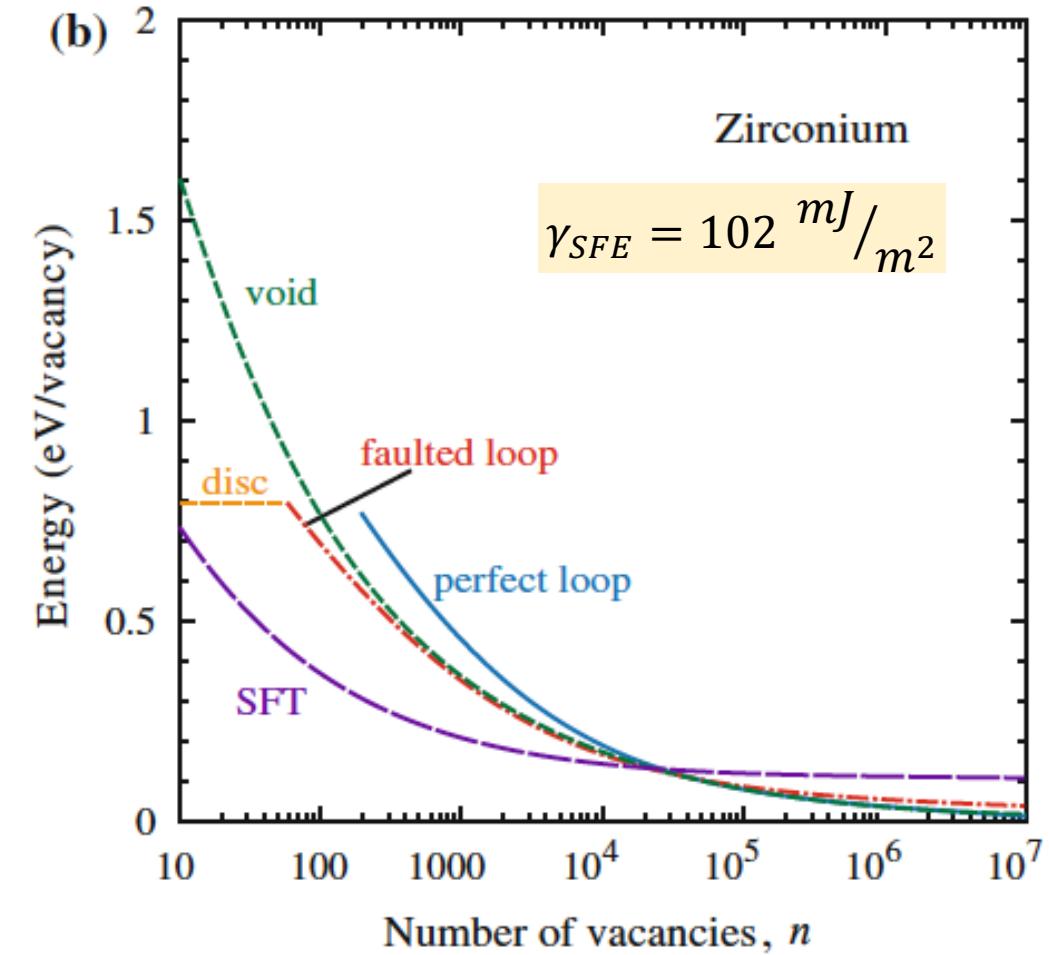
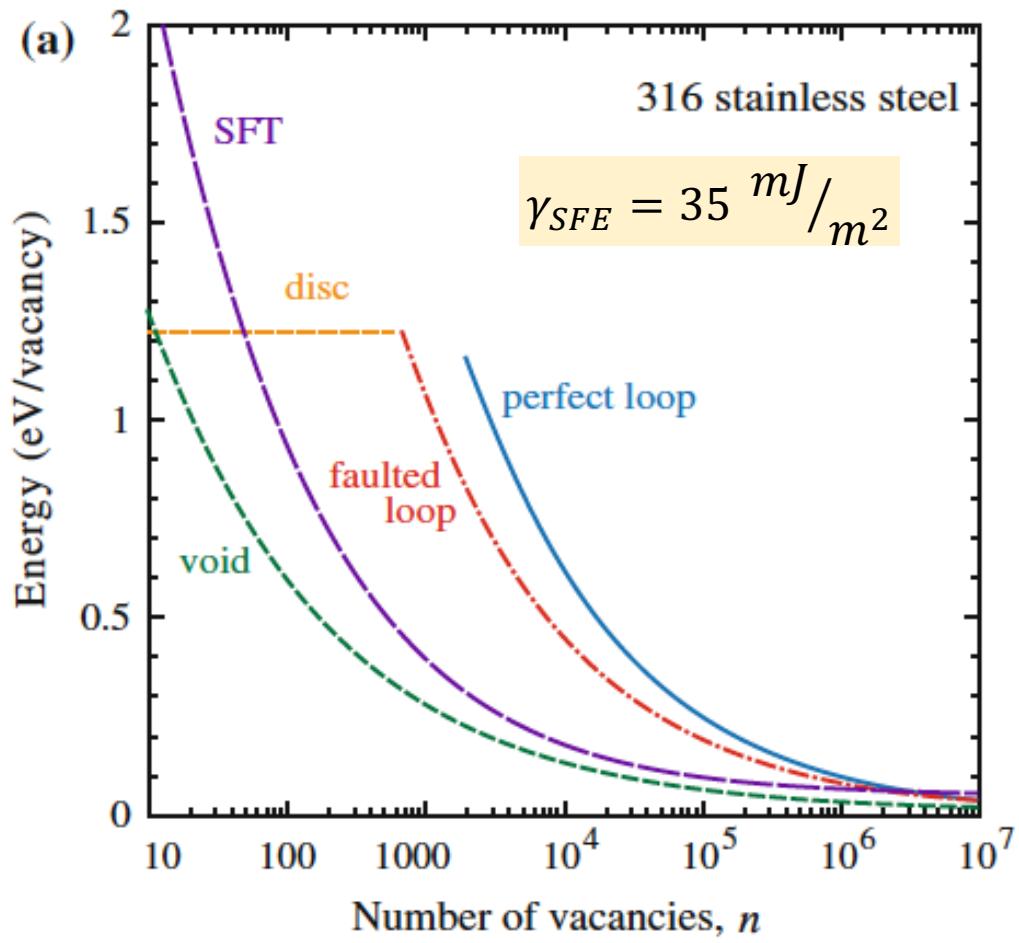


$$\therefore E_s = 4\pi r^2 \sigma \rightarrow E_c = 2\pi r^2 \sigma$$

- For the same n_v , $E_c > E_s$ meaning an activation energy is required to generate loops



Visualizing the energetics

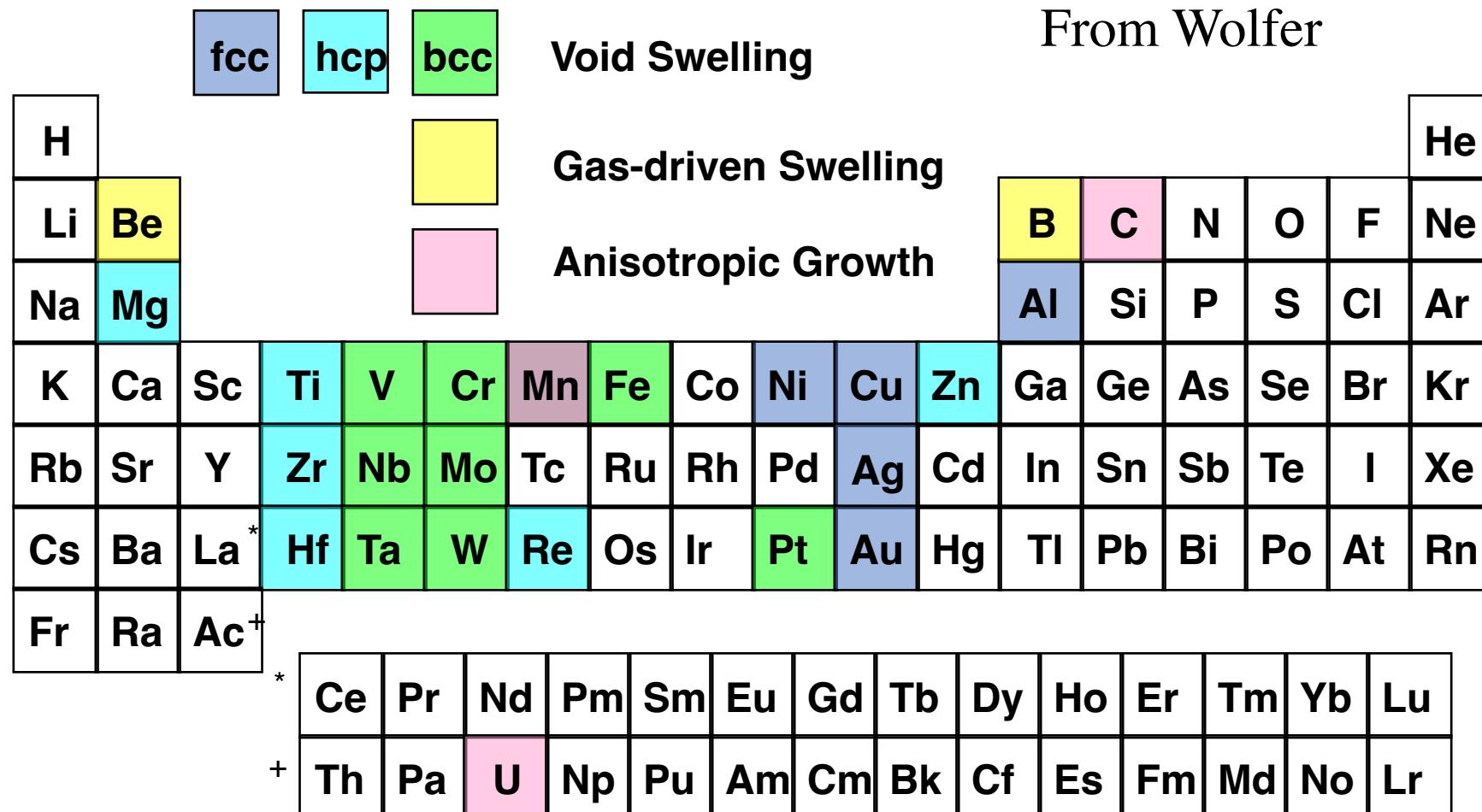


Voids formed in metals

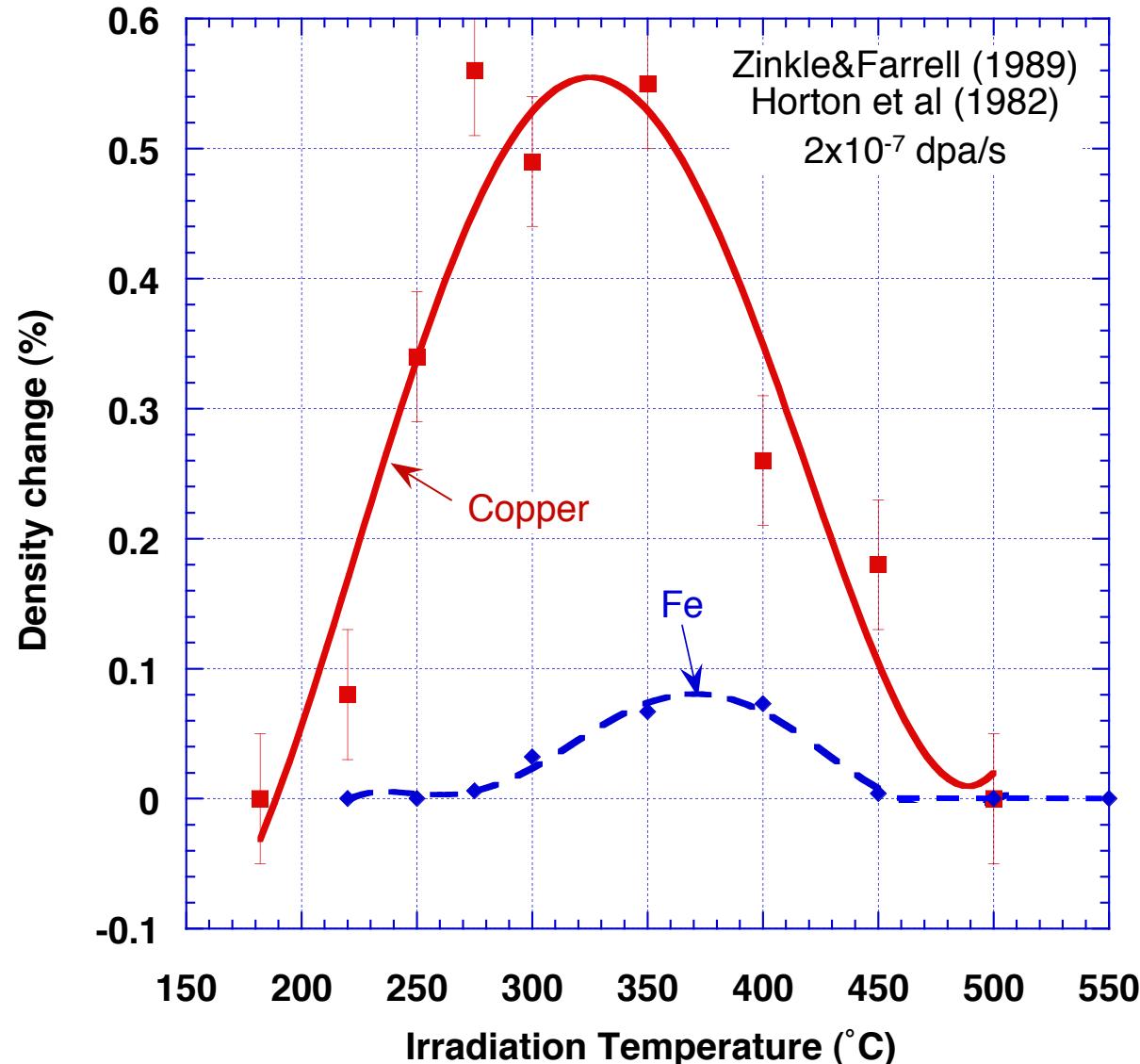
- Voids form by vacancy condensation. Vacancies are supersaturated in irradiated metals.
- Void formation requires “bias” or preferential absorption of self-interstitials at dislocations or other sinks, relative to vacancies
 - V - I recombination is an “unbiased” process since it removes vacancies and interstitials at the same rate
 - Cavities are unbiased sinks for point defects
 - Because of dislocation bias, slightly more interstitials (~20%) are absorbed by dislocations, leaving a slight excess of vacancies to first nucleate and then grow voids.
- These processes are very sensitive to gas pressure in the cavity
 - A void has no gas (in practice, could have very low levels of gas atoms)
 - Impurity atoms within the metal (e.g., O, N) and He produced by (n,a) reactions or by direct implantation are the principal radiation-produced gases that can be trapped by cavities.



Effect of materials variables on void growth

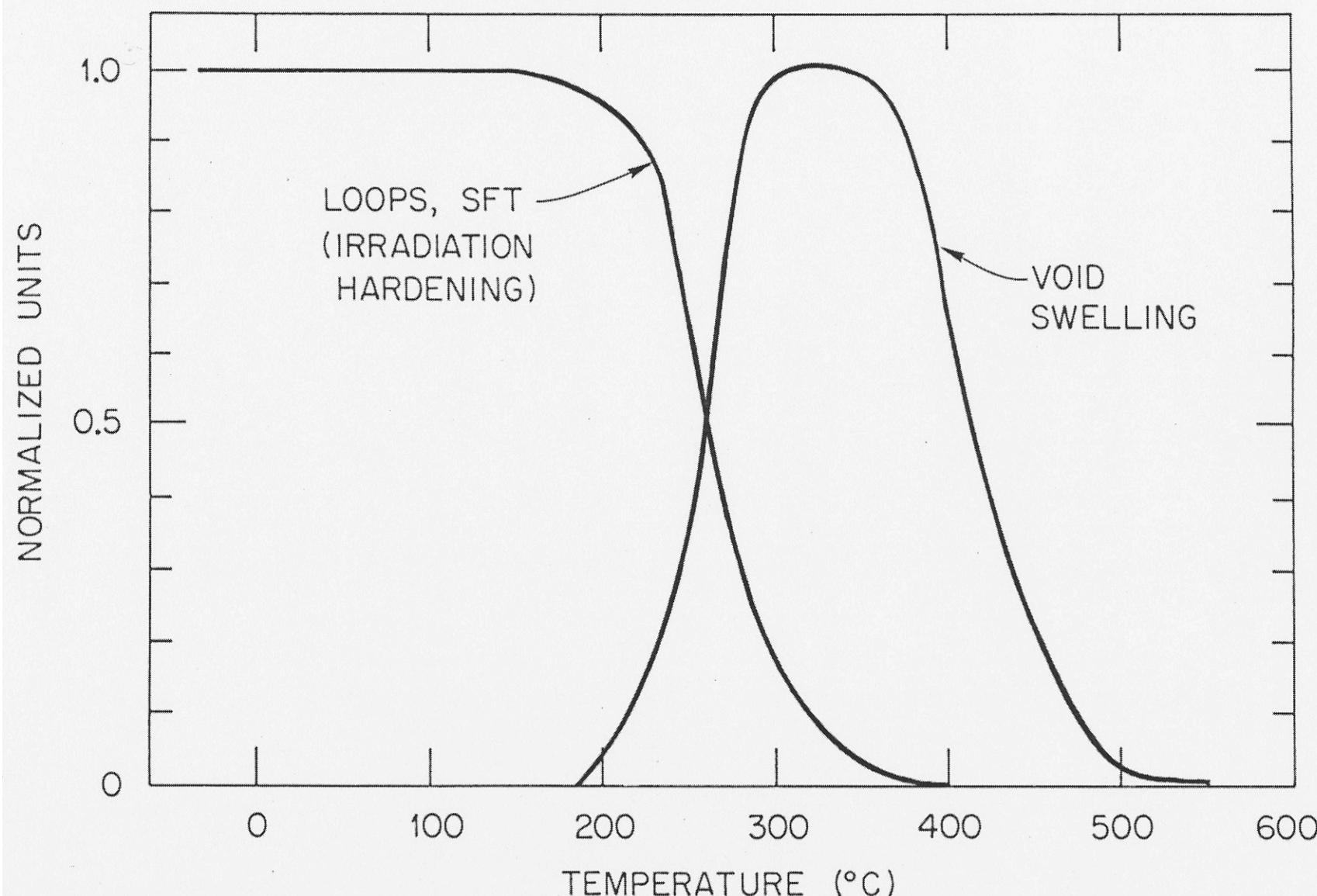


Comparison of Temperature-Dependent Void Swelling in Neutron Irradiated Cu and Fe at 1 dpa



Void swelling is typically of concern for irradiation temperatures between ~ 0.3 and $\sim 0.6 T_M$

Temperature dependence for void swelling involves balance between recombination and vacancy emission

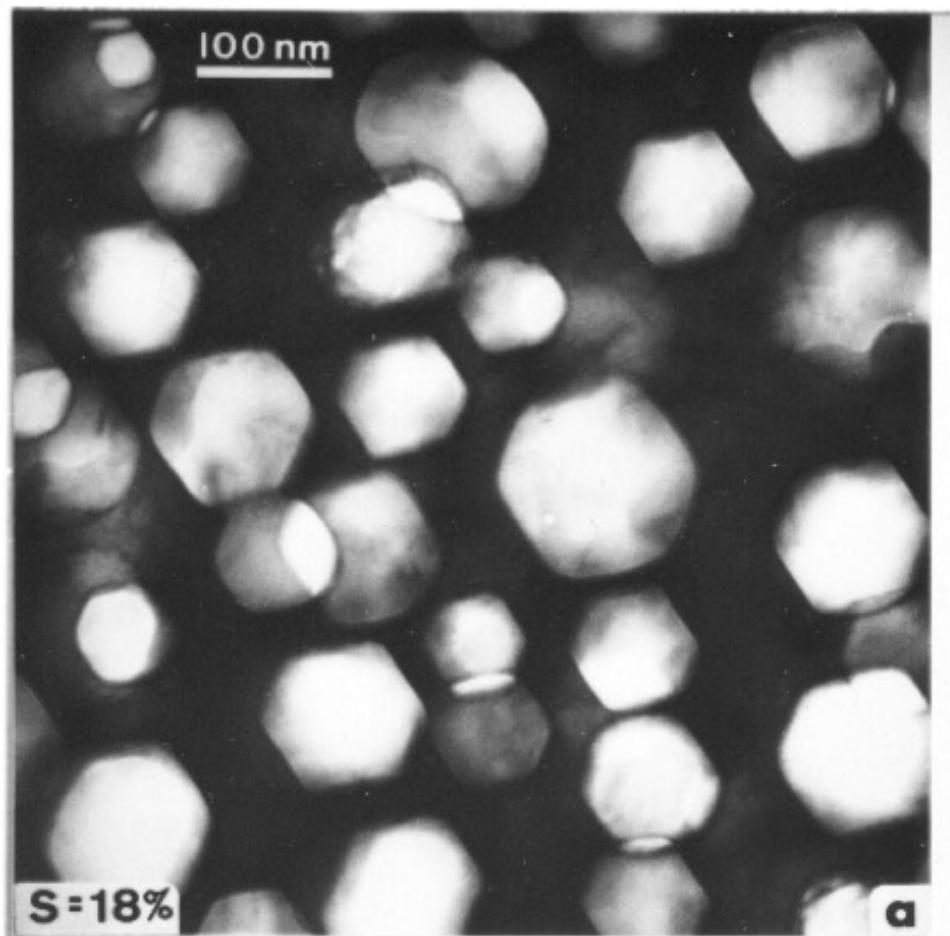


Zinkle, ASTM STP 1125 (1992) p. 813



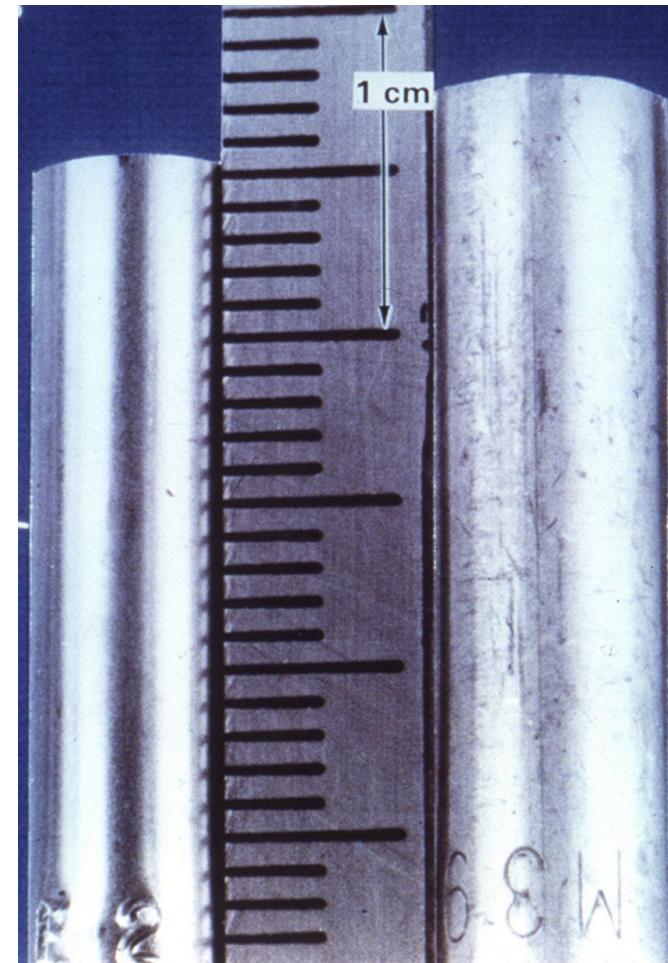
Physical effect of void formation in a material

ion-irradiated austenitic stainless steel
(625°C, 70 dpa)



N. Packan & K. Farrell, J. Nucl. Mater. 85&86 (1979) 677

neutron irradiated 20%CW 316 steel at
T=523°C, $1.5 \times 10^{23} \text{n/cm}^2$



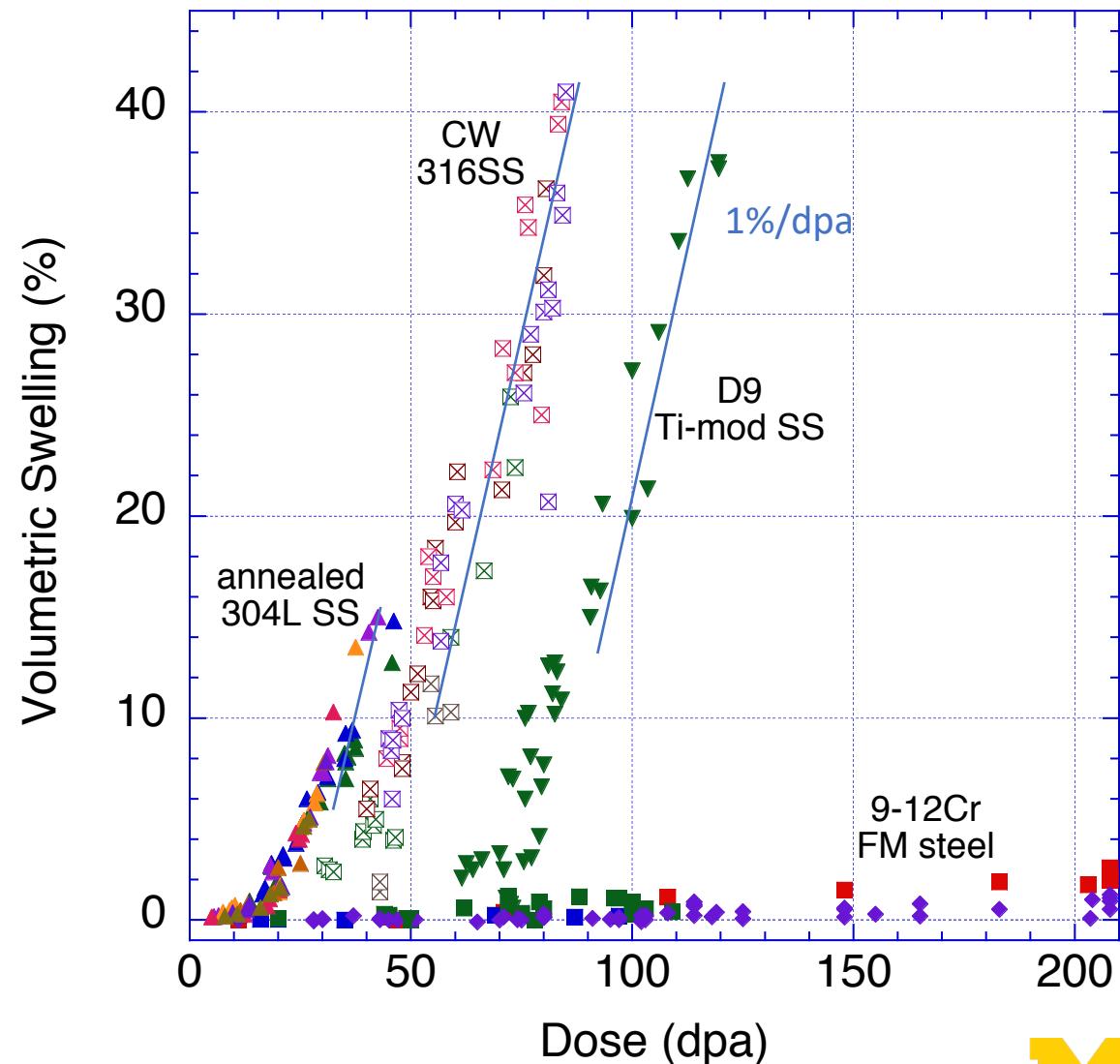
J.L. Straalsund et al., J. Nucl. Mater. 108&109
(1982) 299

Physical effect of void formation in a material

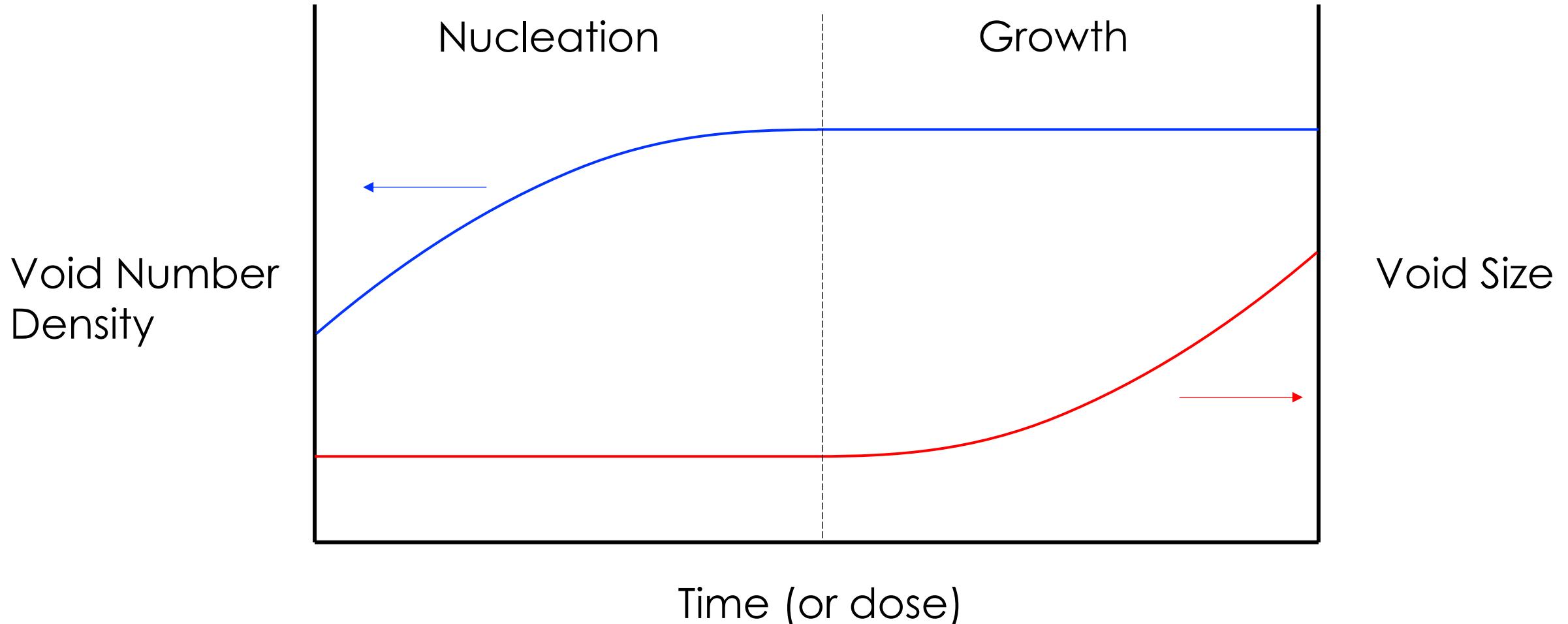
Dimensional changes >5-10 vol.% are unacceptable for typical engineering designs

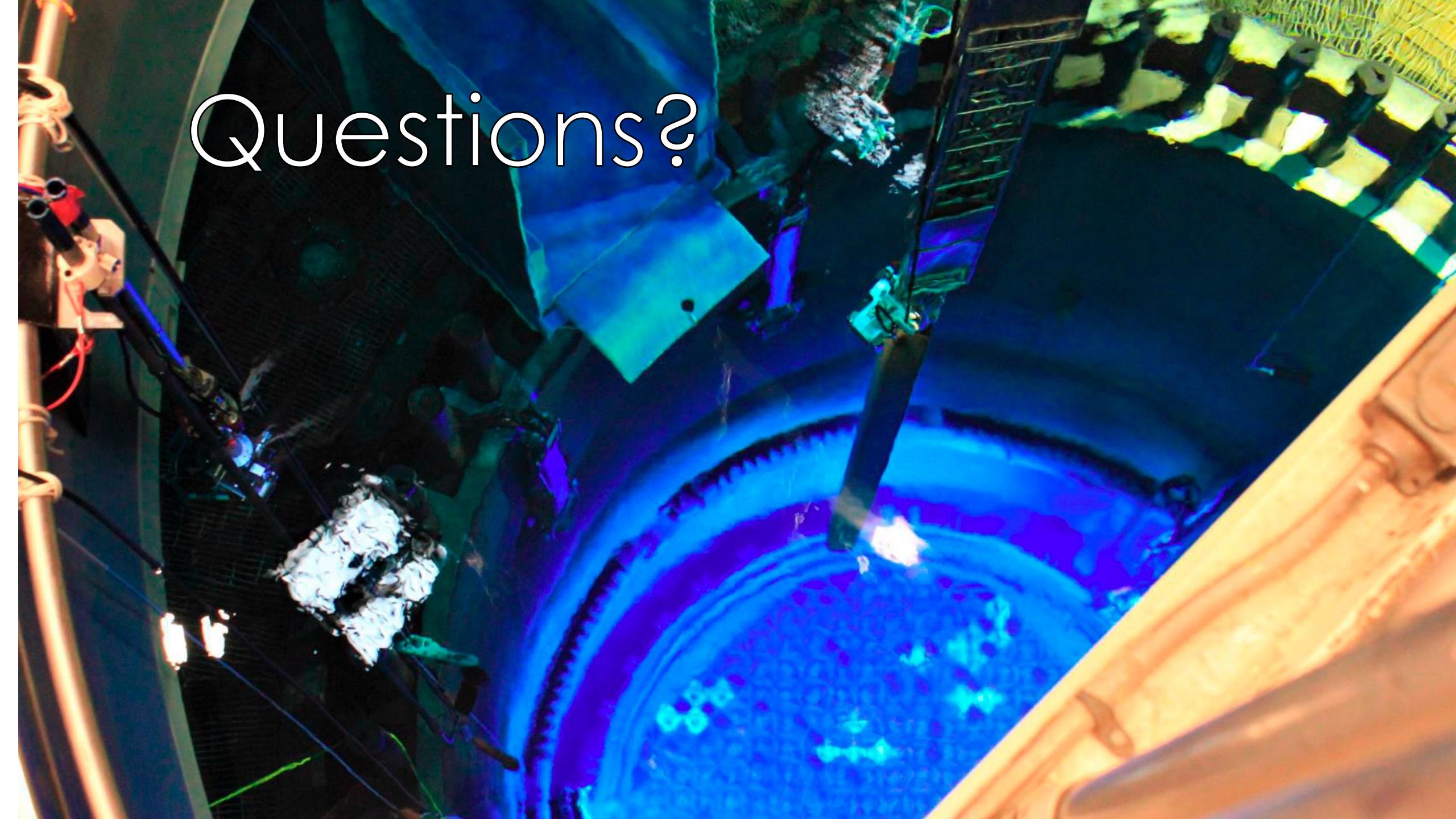
E.g., linear dimensional change due thermal expansion in 316SS between room temperature and 500°C is:

$$DI = a\Delta T = 18 \times 10^6 / ^\circ C * 480^\circ C = 0.86\%$$



Nucleation vs. Growth





Questions?